

- Drafts
- Pending
- Active
 - L1: (1) ("5959308").PN.
 - L2: (1) ("5879962").PN.
 - L3: (1) ("5473174").PN.
 - L4: (1) ("5308444").PN.
 - L5: (1) ("5438851").PN.
 - L6: (1) ("5238869").PN.
 - L7: (1) ("5183776").PN.
 - L8: (1) ("5141693").PN.
 - L9: (1) ("5291321").PN.
 - L10: (1) ("6107635").PN.
 - L11: (0) ("GaAs and (Germanium) and annealing").PN.
 - L12: (778) GaAs and (silicon Si) and SiGe and annealing and (Ge germanium)
 - L13: (0) GaAs and (silicon Si) and SiGe and hight near temperature near annealing and (Ge germanium)
 - L14: (341) GaAs and (silicon Si) and SiGe and annealing and (Ge germanium) and ("70" wt% 70%)
 - L15: (19) GaAs and (silicon Si) and SiGe and annealing and (Ge germanium) and ("70" wt% 70%)
- Failed
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ପ୍ରକାଶକ ପରିଷକ୍ଷାରେ ୧୯ ପ୍ରକାଶକ ପରିଷକ୍ଷାରେ ପ୍ରକାଶନ କରାଯାଇଥିବା

Ge45 and (SiGe) and 5Ge and annealing and (Ge germanium) and ((78% wt% 70% wt% Ge))

Ge

Order	Document ID	Issue Date	Pages	Title	Current CR	Current XRef
1	US 20050023552 A1	20050203	8	Growth of GeSi epitaxial layers on Si substrate by using a novel GeSi buffer layer	257/103	
2	US 20040256613 A1	20041223	35	Semiconductor device, semiconductor circuit module and manufacturing method of the same	257/19	257/E21.066; 257/E21.633; 257/E27.064
3	US 20040157412 A1	20040812	12	Method to produce germanium layers	438/478	257/E21.129; 257/E21.131; 438/483
4	US 20040137685 A1	20040715	19	Gate material for semiconductor device fabrication	438/285	257/E21.202; 257/E21.203; 257/E21.334
5	US 20040115916 A1	20040617	28	Selective placement of dislocation arrays	438/597	
6	US 20040092051 A1	20040513	12	Methods for preserving strained semiconductor substrate layers during CMOS processing	438/22	257/18; 257/19
7	US 20040072409 A1	20040415	17	Coplanar integration of lattice-mismatched semiconductor with silicon via wafer bonding via structures	438/455	257/E21.568; 257/E21.569; 438/459
8	US 20040031979 A1	20040219	64	Strained semiconductor-on-insulator device structures	257/233	257/233; 257/297; 257/E21.415
9	US 20040005740 A1	20040108	35	Strained semiconductor-on-insulator device structures	438/149	257/347; 257/349; 257/357
10	US 20030227057 A1	20031211	21	Strained semiconductor-on-insulator device structures	257/347	257/E21.415; 257/E21.442;
11	US 20020106882 A1	20020808	7	Method of producing a semiconductor layer on a substrate	438/605	257/E21.57; 438/201